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# FDC645N

# N-Channel PowerTrench® MOSFET

#### **General Description**

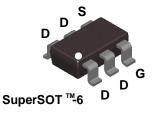
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{\text{DS(ON)}}$  and fast switching speed.

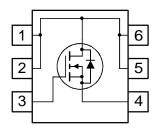
#### **Applications**

• DC/DC converter

#### **Features**

- 5.5 A, 30 V.  $R_{DS(ON)} = 30 \text{ m}\Omega$  @  $V_{GS} = 4.5 \text{ V}$   $R_{DS(ON)} = 26 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS(ON)}}$
- Low gate charge (13 nC typical)
- High power and current handling capability





### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		±12	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	5.5	А
	- Pulsed		20	
P <sub>D</sub>	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
$T_J, T_{STG}$	Operating and Storage Junction Tem	perature Range	-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{ heta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

**Package Marking and Ordering Information** 

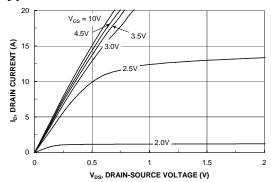
•	Device Marking	Device	Reel Size	Tape width	Quantity
	.645	FDC645N	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1		l	l	I
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
<u>ΔBV<sub>DSS</sub></u> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		22		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \ \ V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	0.8	1.4	2	V
$\Delta V_{GS(th)}$ $\Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		- 4		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 6.2 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}, T_J = 125^{\circ}\text{C}$		25 23 34	30 26 48	mΩ
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 5 V	20			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 5.5 \text{ A}$		33		S
Dynamic	Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		1460		pF
Coss	Output Capacitance	f = 1.0 MHz		227		pF
Crss	Reverse Transfer Capacitance	7		96		pF
Switchir	g Characteristics (Note 2)	•				
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DS} = 15 \text{ V},  I_{D} = 1 \text{ A},$		8	16	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	7		35	56	ns
t <sub>f</sub>	Turn-Off Fall Time	1		7	14	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 6.2 \text{ A},$		13	21	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 4.5 V		nC		
$Q_{gd}$	Gate-Drain Charge	1		3.6		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings	•	•	•	
ls	Maximum Continuous Drain-Source				1.3	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V},  I_{S} = 1.3 \text{ A}$ (Note 2)		0.7	1.2	V

#### Notes:

- R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.
  - a.  $78^{\circ}\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2oz copper on FR-4 board.
  - b. 156°C/W when mounted on a minimum pad.
- 2. Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$

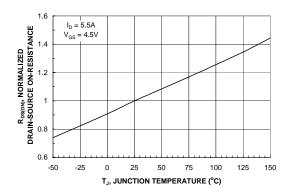
## **Typical Characteristics**



1.4 V<sub>GS</sub> = 3.0V V<sub>GS</sub> = 3.5V V

Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



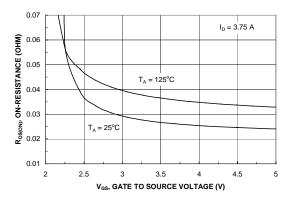
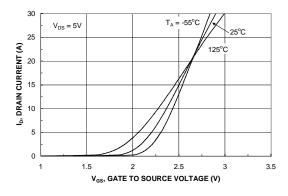


Figure 3. On-Resistance Variation withTemperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



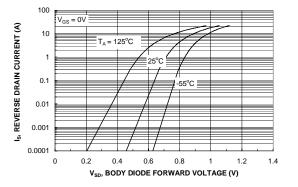


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## **Typical Characteristics**

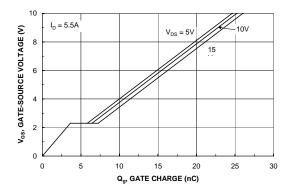
R<sub>DS(ON)</sub> LIMIT

SINGLE PULSE R<sub>θJA</sub> = 156°C/W T<sub>A</sub> = 25°C

ID, DRAIN CURRENT (A)

10

0.01



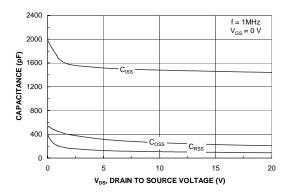


Figure 7. Gate Charge Characteristics.

10ms

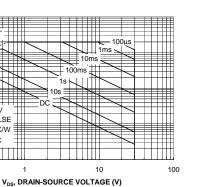


Figure 8. Capacitance Characteristics.

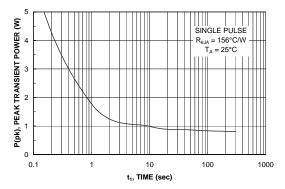


Figure 9. Maximum Safe Operating Area.



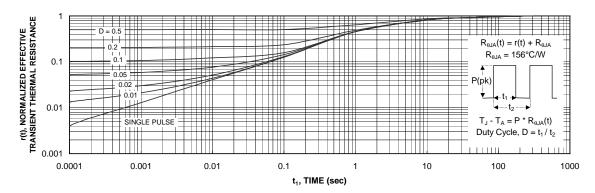


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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